

CMXSH-3

**SURFACE MOUNT
TRIPLE ISOLATED
SILICON SCHOTTKY DIODES**



www.centrasemi.com



DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXSH-3 type contains three (3) Isolated Schottky Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for applications requiring low forward voltage drop.

MARKING CODE: XH3

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Continuous Forward Current	I_F	100	mA
Peak Repetitive Forward Current	I_{FRM}	350	mA
Peak Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	750	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C/W}$

SYMBOL

V_{RRM}	30	V
I_F	100	mA
I_{FRM}	350	mA
I_{FSM}	750	mA
P_D	350	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	357	$^\circ\text{C/W}$

UNITS

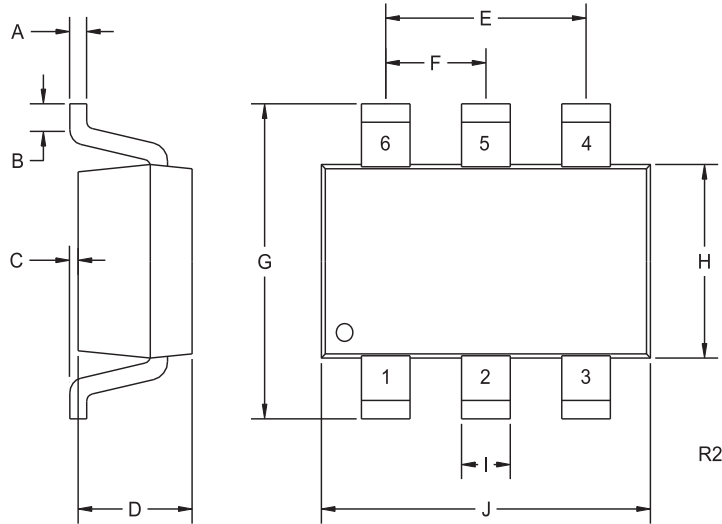
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=25\text{V}$		90	500	nA
I_R	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	μA
BV_R	$I_R=100\mu\text{A}$	30			V
V_F	$I_F=2.0\text{mA}$		0.29	0.33	V
V_F	$I_F=15\text{mA}$		0.40	0.45	V
V_F	$I_F=100\text{mA}$		0.74	1.00	V
C_T	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

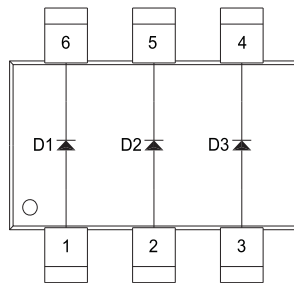
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SOT-26 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

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R5 (12-February 2010)